

				MicroNanoTechnology
ſ	Semestral Project	☐ Master Project	☐ Thesis	▼ Other

Fabrication of High Aspect Ratio Silicon Mold

Description of the fabrication project

The goal is to to fabricate cavities (trenches and holes) in silicon that could later serve to create metallic pieces at the small scale. We will use deep reactive ion etching to create 2.5D shaped components in silicon, and different coating processes to deposit a protection layer on top.

Technologies used				
Mask fabrication, sputtering, evaporation, positive resist, Dry etching, Wet etching, Electro-Plating, Dicing, SEM				
Ebeam litho data - Photolitho masks - Laser direct write data				
Mask #	Critical Dimension	Critical Alignment	Remarks	
1	10 μm	First Mask	Mold shape	
Substrate Type				
4 inch Si{100} wafer with 2um SiO2				

Interconnections and packaging of final device

Thinning No	g/grinding/polishing of the samples is required at some stage of the process. Yes => confirm involved materials with CMi staff		
Dicing of	f the samples is required at some stage of the process. Ves => confirm dicing layout with CMi staff		
Wire-bonding of dies, with glob-top protection, is required at the end of the process. ✓ No ☐ Yes ⇒ confirm pads design (size, pitch) and involved materials with CMi staff			



Step-by-step process outline

Step	Process description	Cross-section after process
01	Photolith PR Coat Machine: Süss ACS200 PR: AZ10XT-20 (HDMS) Thickness: 4 μm	
02	Photolith expo + develop Machine: MLA150	
03	Hard Mask Etching Machine: SPTS APS Diele etcher Material: SiO ₂ Depth: 2μm	
04	DRIE Bosch Process Machine: Rapier etcher Material: Si Depth: 250-500 μm Inner width: 25-50 μm Outer width: 75-175 μm	
05	O2 plasma treatment Machine: Tepla 300 Time: 10 min (high power)	



06	Oxide layer deposition Machine: Thermal Process, CMi Material: SiO ₂ Thickness: 2 µm Preprocessing: RCA cleaning	
07	Dicing (with UV-tape top proctection) Dimensions: 9x9 mm2	